

AMENDMENTS TO THE CLAIMS:

This listing of claims replaces all prior listing of claims in this application.

Claims 1-86 (canceled).

87. (Currently Amended) A method of forming a structure for supporting an integrated circuit chip, which chip may be affected by external magnetic fields, said method comprising:

forming a substrate;

forming a layer of magnetic field shielding material over said substrate;

forming an insulating layer over ~~a first surface of said substrate~~ said layer of magnetic field shielding material;

providing a support surface for an integrated circuit chip, said substrate, layer of magnetic field shielding material, insulating layer and support surface forming part of a chip carrier; and

supporting an integrated circuit chip with said chip carrier, said chip carrier having a top and bottom surface. [[;]] and

~~providing at least one layer of magnetic field shielding material in contact with said integrated circuit chip which shields said integrated circuit chip from external magnetic fields.~~

88. (Currently Amended) The method of claim 87, further comprising providing a second layer of magnetic field shielding material ~~between said insulating layer and said first surface of said substrate on top of said chip carrier.~~

89. (Currently Amended) The method of claim 87, further comprising providing a second layer of magnetic field shielding material embedded within said substrate of said chip carrier.

90. (Currently Amended) The method of claim 87, further comprising providing a second layer of magnetic field shielding material ~~on both a bottom surface and a top surface of said~~ embedded within a printed circuit board electrically coupled to said chip carrier.

91. (Original) The method of claim 87, wherein said semiconductor device is a magnetic memory device.

92. (Original) The method of claim 91, wherein said magnetic memory device is a magnetic random access memory device.

93. (Original) The method of claim 87, wherein said layer of magnetic field shielding material comprises a magnetic material selected from the group consisting of ferrites, manganites, chromites and cobaltites.

94. (Original) The method of claim 93, wherein said magnetic material comprises MFe_2O_4 , wherein M is at least one atom selected from the group consisting of Mn, Fe, Co, Ni, Cu, and Mg.

95. (Original) The method of claim 93, wherein said magnetic material comprises a material which includes conductive particles.

96. (Original) The method of claim 95, wherein said conductive particles are selected from the group consisting of nickel particles, iron particles, and cobalt particles.

97. (New) The method of claim 87, further comprising providing a second layer of magnetic field shielding material formed on a chip electrically coupled to said chip carrier.

98. (New) The method of claim 87, further comprising providing a second layer of magnetic field shielding material on the bottom surface of said chip carrier.

99. (New) The method of claim 87, further comprising providing a second layer of magnetic field shielding material on the top surface of said chip carrier.